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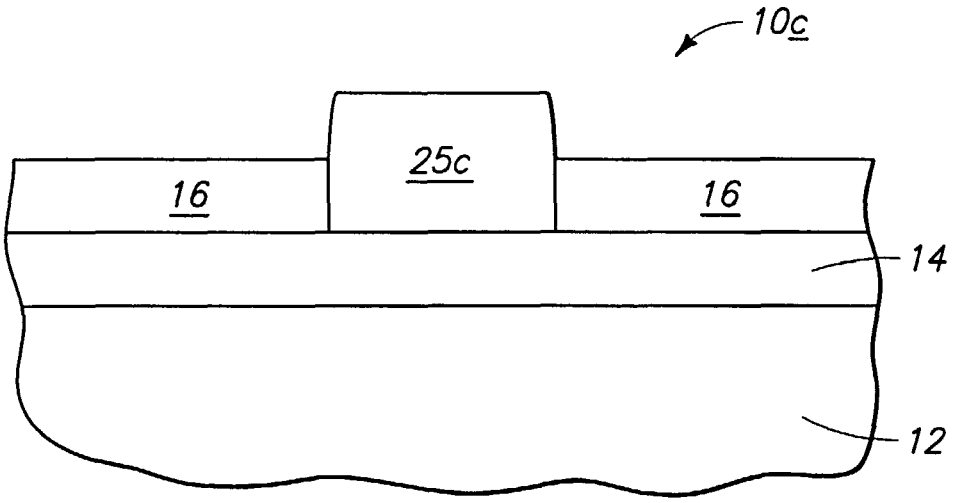
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(54) Title: METHODS OF FORMING NON-VOLATILE RESISTANCE VARIABLE DEVICES AND METHODS OF FORMING SILVER SELENIDE COMPRISING STRUCTURES



(57) Abstract: A method of forming a non-volatile resistance variable device includes forming a patterned mass comprising elemental silver over a substrate. A layer comprising elemental selenium is formed over the substrate and including the patterned mass comprising elemental silver. The substrate is exposed to conditions effective to react only some of the elemental selenium with the elemental silver to form the patterned mass to comprise silver selenide. Unreacted elemental selenium is removed from the substrate. A first conductive electrode is provided in electrical connection with one portion of the patterned mass comprising silver selenide. A germanium selenide comprising material is provided in electrical connection with another portion of the patterned mass comprising silver selenide. A second conductive electrode is provided in electrical connection with the germanium selenide comprising material.

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